

Lecture 3 - Ionic Conductivity

Lecture summary

- Recap of defect types
- Ionic conductivity
- Conduction mechanisms
- Ionic migration paths
- Energetics of conduction

Defect recap



Defect recap results

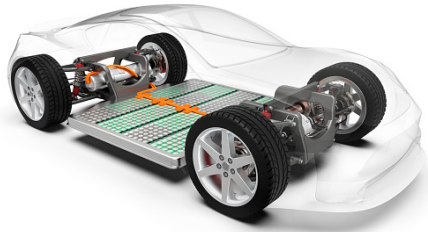
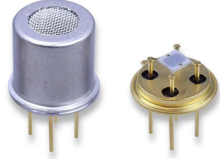
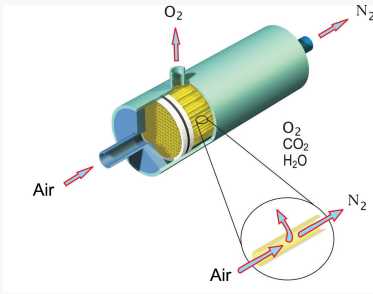

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Conductivity

- Many ionic solids conduct electricity; due to *ionic* and/or *electronic* motion.
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- Most ionic solids are electrically insulating/semiconducting (localised electrons)
- Ionic conductors are important!

	
Batteries (Lecture 4)	Sensors
	
Separation Membranes	Fuel Cells (Lecture 6)

Origin of ionic conduction

- Ionic conductivity is dominated by **defects**
 - In an ideal crystal, ions can't easily move
 - vacancies and/or interstitials are the main charge carriers

Origin of ionic conduction

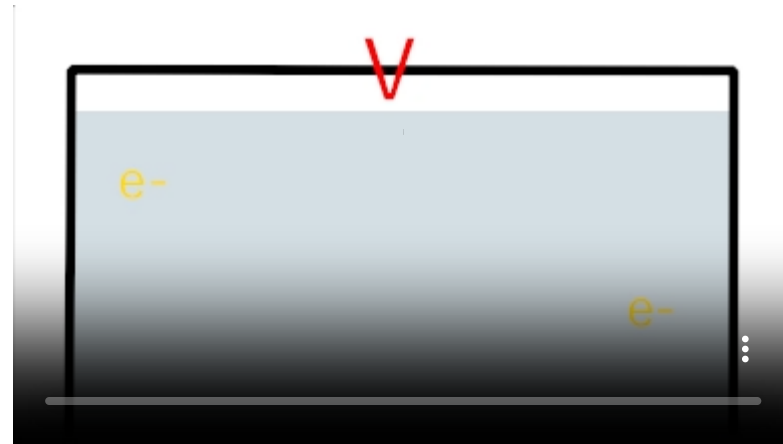
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 - n is number of charge carriers
 - q is charge
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 - n is number of charge carriers
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- In ionic solids, conductivity covers $10^{-16} \text{ S m}^{-1} - 10^3 \text{ S m}^{-1}$
 - most solids are limited to around 10^{-2} S m^{-1}
 - Liquid electrolytes typically $10^{-1} - 10^3 \text{ S m}^{-1}$

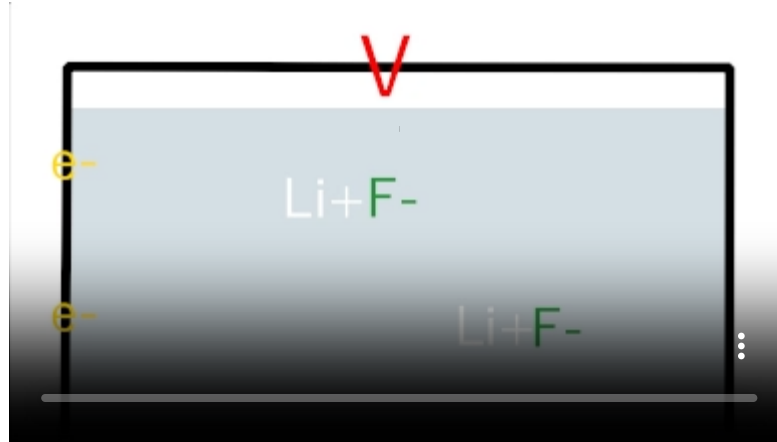
Measuring Conductivity

- For electronic conductors, this is simple:
 - Apply a voltage (V) and measure the resulting current (I)
 - Resistance (in Ω) is found through Ohm's law; $V = IR$
 - Resistivity (in $\Omega \text{ cm}$) of the material calculated from geometry
- Resistivity ρ (in $\Omega \text{ cm}$) = $\frac{1}{\text{Conductivity } \sigma \text{ (in } \text{S cm}^{-1}\text{)}}$



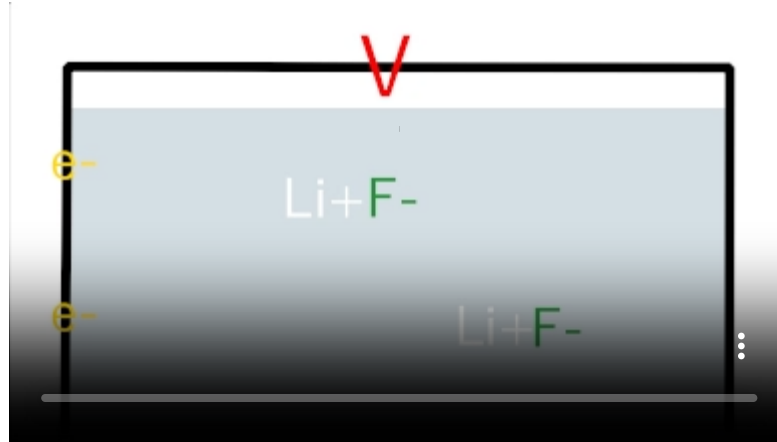
Measuring Ionic Conductivity

- Ions cannot flow round a circuit, so current drops with a constant applied voltage

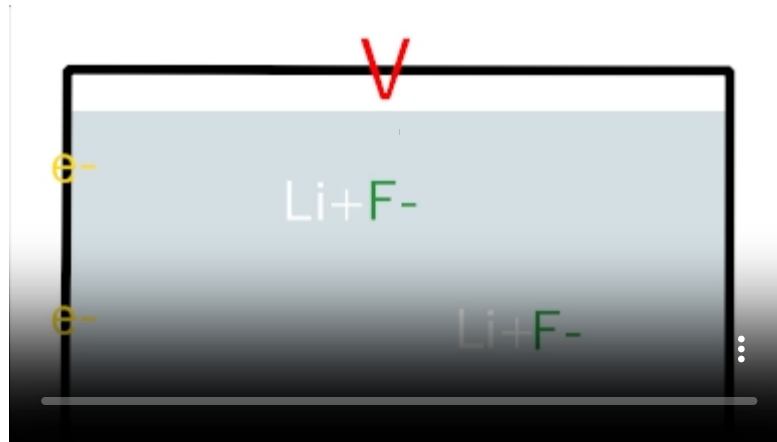


Measuring Ionic Conductivity

- Ions cannot flow round a circuit, so current drops with a constant applied voltage



- Instead, we use an alternating voltage - this is called Impedance spectroscopy (see [lecture 5](#))



Ion migration mechanisms

Three 'main' mechanisms of ionic migration

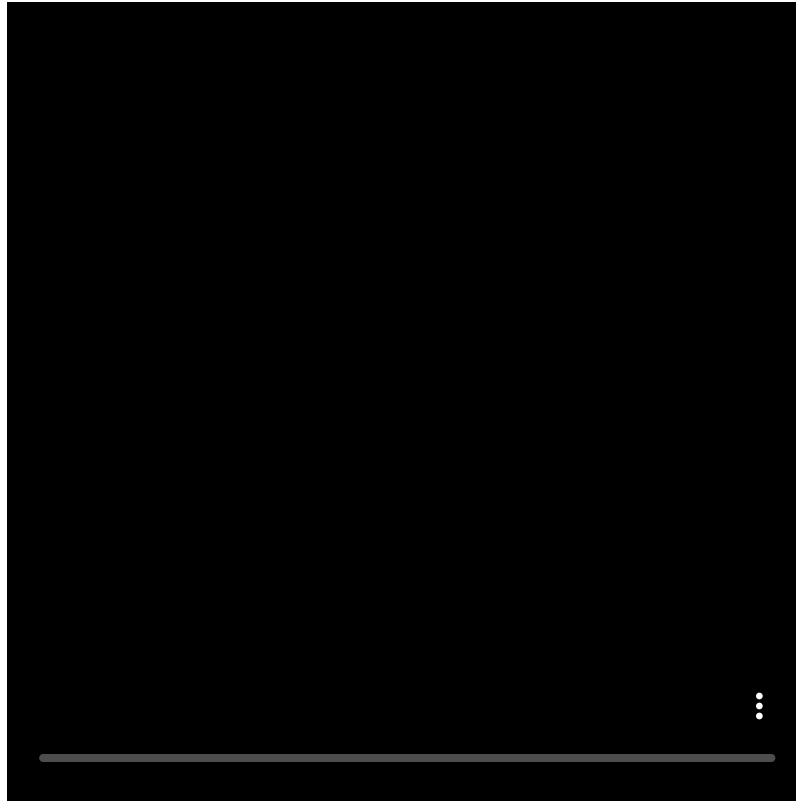
1. Vacancy mechanism

Vacancies move throughout the lattice (atoms move into vacancy)



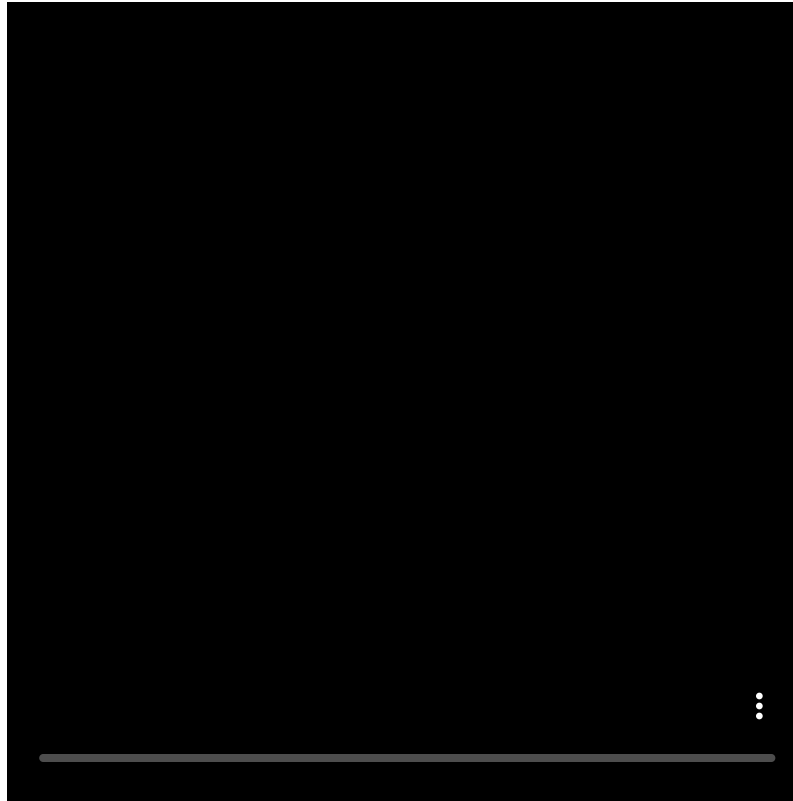
2. Interstitial mechanism

Ions hop between interstitial sites



3. Interstitialcy (knock-on) mechanism

Interstitial ions 'push' into a neighbouring site



Vacancy, Interstitial or Interstitialcy?

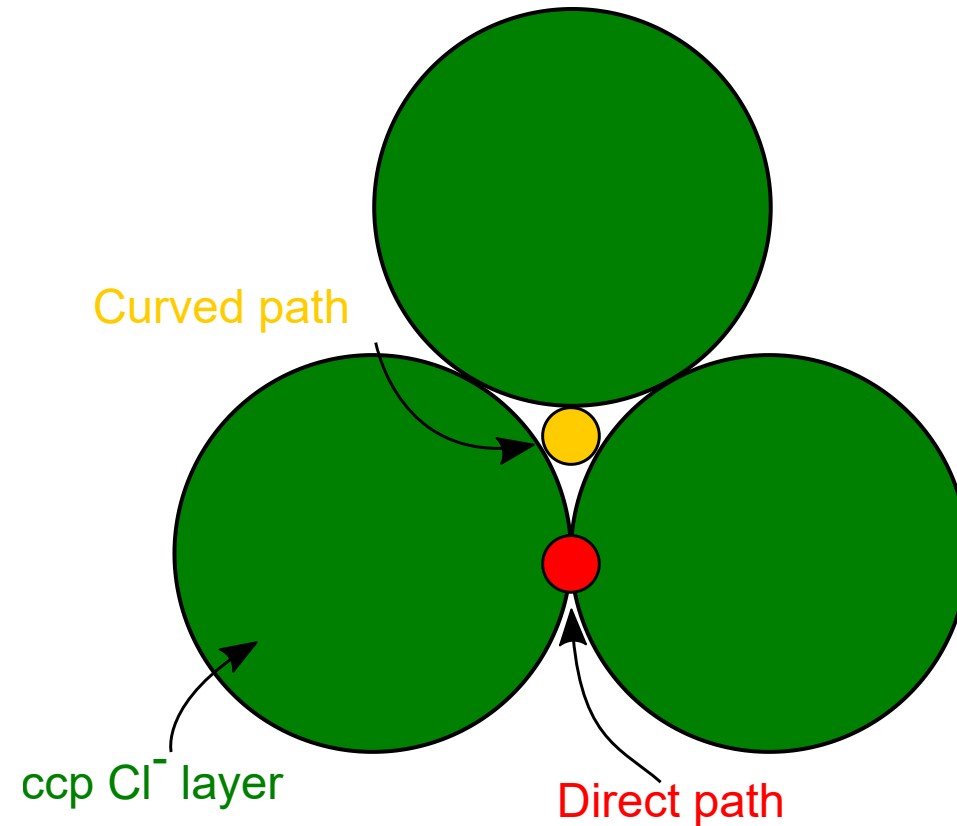
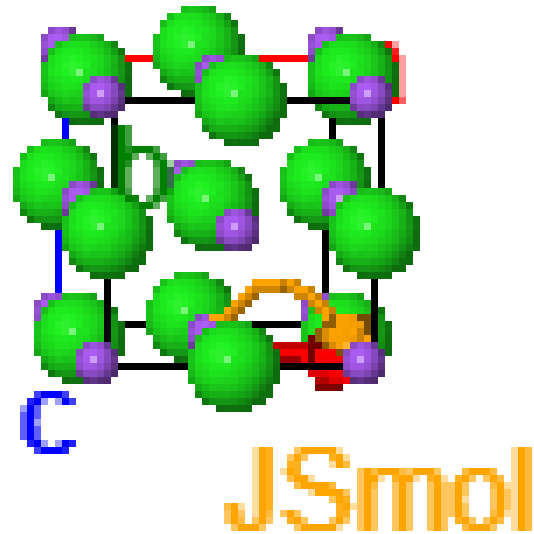


Suggestions

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Migration paths

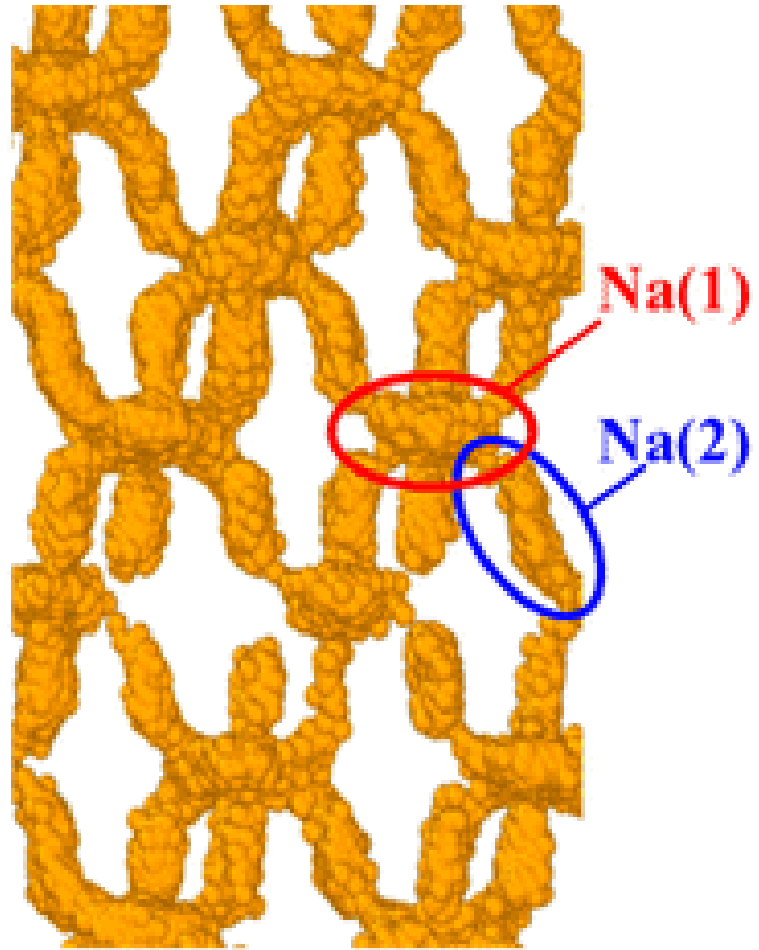
Ion paths are rarely **direct**, but will take the **lowest energy route**.



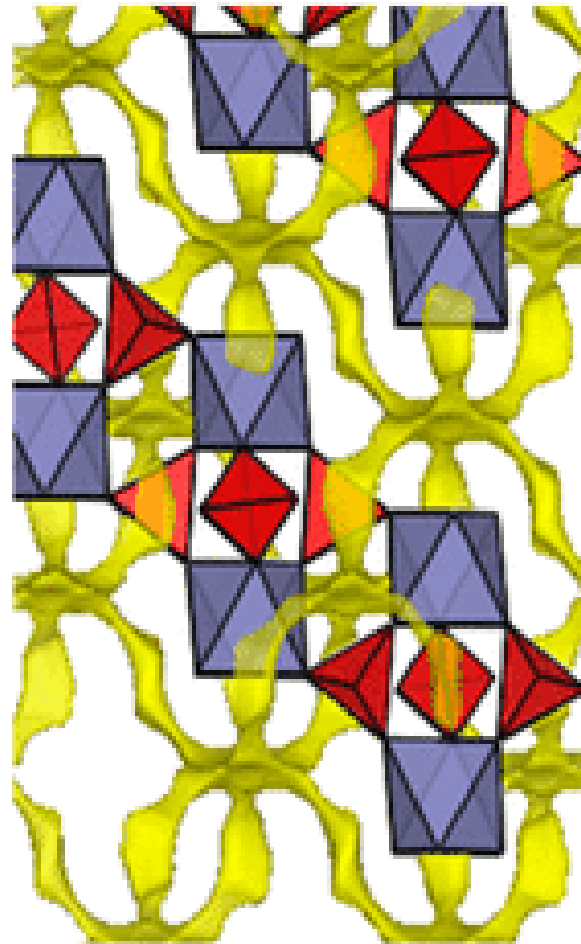
Pathways can be complex

- Migration pathways can be calculated and/or experimentally determined

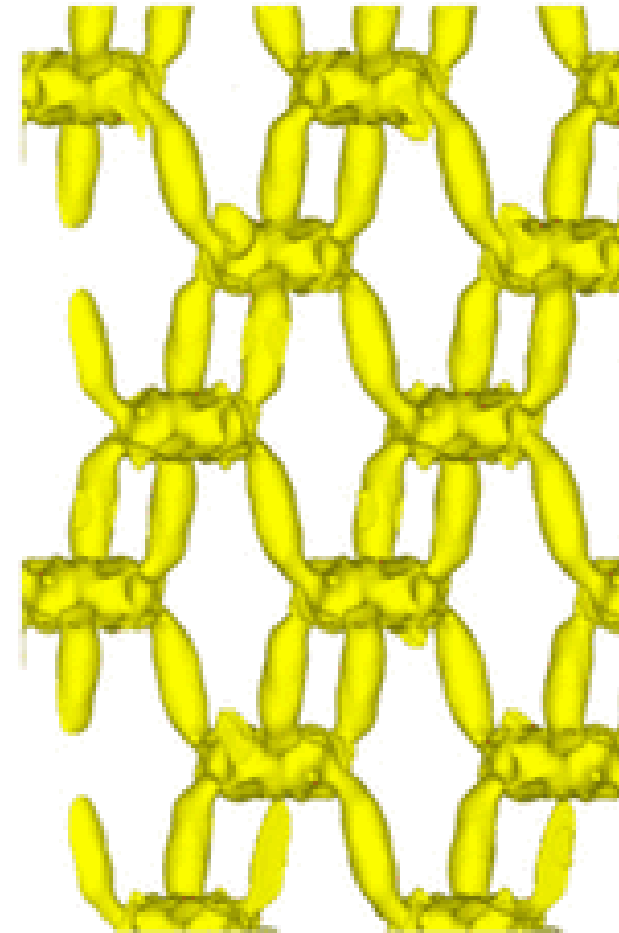
e.g. **NASICON** Na^+ conductor, $\text{Na}_3\text{Zr}_2(\text{SiO}_4)_2(\text{PO}_4)$:



MD density plot



BVEL



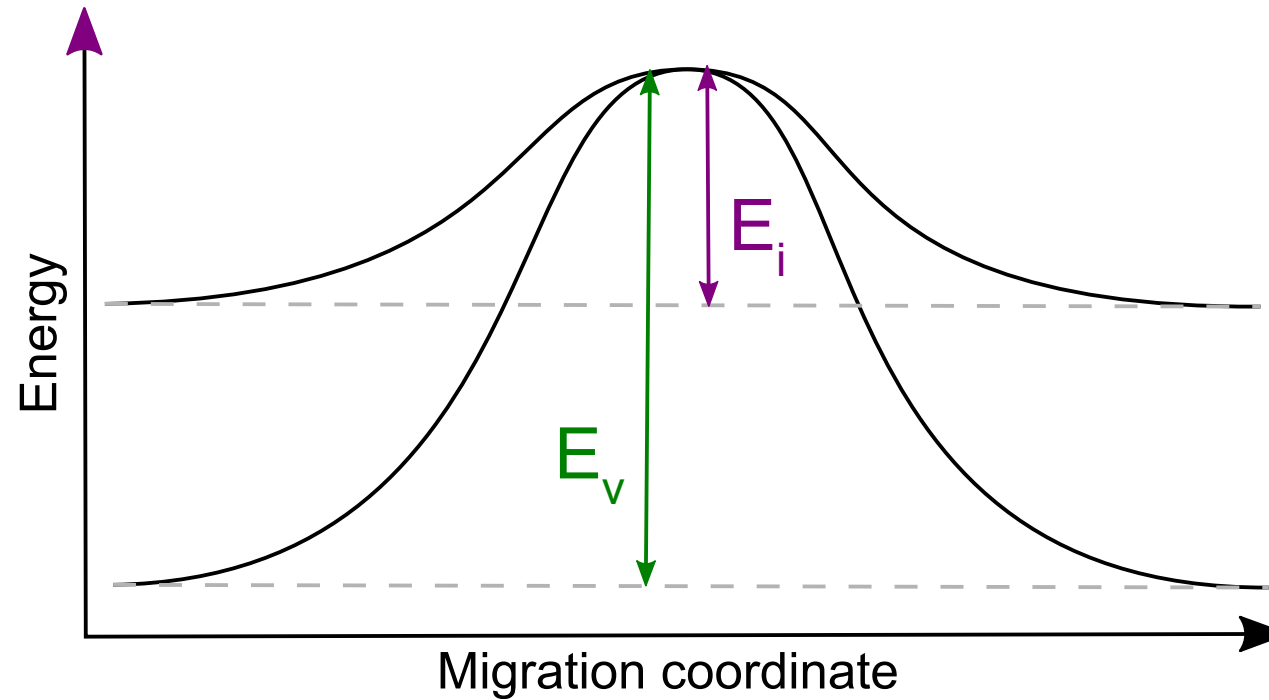
MEM/Rietveld

Migration energetics

- Defect mobility (μ) is a thermally-activated process:

$$\mu = \mu_0 \exp\left(-\frac{E_a}{RT}\right)$$

- interstitial sites are higher energy than vacancies, so will have be more mobile.



Variation with temperature

As $\sigma = nq\mu$ and μ is thermally-activated,

$$\begin{aligned}\sigma &= nq\mu_0 \exp\left(-\frac{E_a}{RT}\right) \\ &= A \exp\left(-\frac{E_a}{RT}\right)\end{aligned}$$

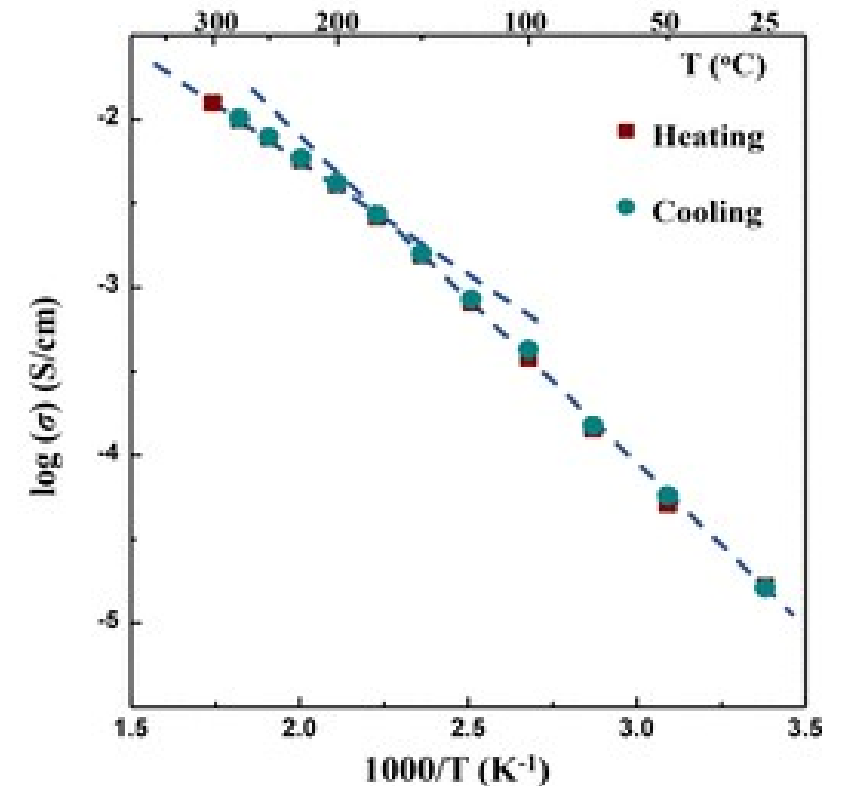
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Plotting $\ln \sigma$ vs. $\frac{1}{T}$ should give a straight line

- more commonly we plot $\log_{10} \sigma$ vs. $\frac{1000}{T}$ for high temperature measurements
- gradient is $\frac{-E_a}{R}$ (or $\frac{-E_a}{2303R}$ using base 10).



Lecture recap

- Defects can give rise to ionic conduction
 - Occurs by three main mechanisms:
 - Vacancy hopping
 - Interstitial hopping
 - interstitialcy (knock-on) cooperation
- Ionic conductivity is thermally-activated
 - shows Arrhenius-like behaviour
- Different defects have different conduction energetics
 - Pathways can sometimes be determined experimentally

Feedback



